

Photo Transistor

General Purpose 4 and 6 Pin DIP

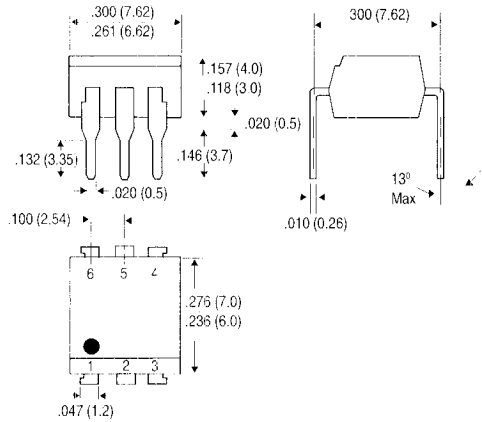
Part Number	Features	Current Transfer Ratio I _F = 10mA Min (%)		Isolation Test Voltage (V) Peak	Continuous Forward Current Max (mA)	VBR I _R = 10μA Min (V)	BV _{CEO} I _C = 1mA Min (V)	I _{CEO} (Dark) V _{CE} = 10V Max (nA)	V _{CE} (Sat) I _F = 16mA I _C = 2mA Max(V)	Schematic No.	Package No.
H24A1	4 Pin Package	100		5300	60	3.0	30	100	0.4 (I _F = 10mA) (I _C = 0.5mA)	3	4
H24A2		20									
H24A3		75									
H24A4		50									
H11A1	6 Pin DIP Optically Coupled pair with Infrared Emitting Diode and Silicon Photo Transistor	50		3500		70	50	0.4	5	2	
IL2 NEW		100	30 (I _F = 1mA)	7500							
IS1		20		3500		30	100	0.5 (I _C = 1.5mA)			
IS5		50						0.5 (I _C = 0.5mA)			
IS74		12.5 (I _F = 16mA)						0.4 (I _F = 10mA) (I _C = 2mA)			
MCT2		20						0.4 (I _F = 10mA) (I _C = 2mA)			
MCT2E		50									
TIL111		12.5 (I _F = 16mA) V _{CE} = 0.4V									
SFH609-1		40 - 80		5300		6.0	90				50
SFH609-2		63 - 125									
SFH609-3		100 - 200									
											100

High Collector-Emitter Voltage

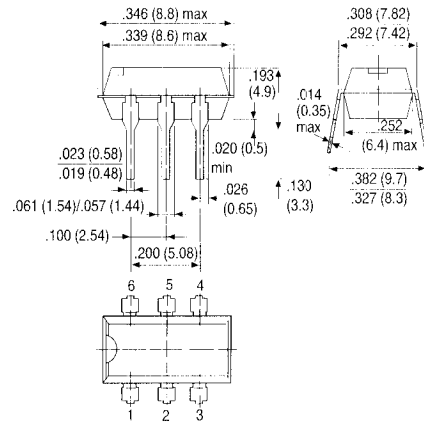
Part Number	Features	Current Transfer Ratio I _F = 10mA Min (%)	Isolation Test Voltage (V) Peak	Continuous Forward Current Max (mA)	Forward Voltage I _F = 10mA Max (V)	BV _{CEO} I _C = 1mA Min (V)	I _{CEO} (Dark) Max (nA)	V _{CE} (Sat) I _F = 10mA I _C = 0.5mA Max(V)	Schematic No.	Package No.
H11D1	Optically Coupled pair with Infrared Emitting Diode and Silicon High Voltage Transistor	20	7500	60	1.5	300	100 (V _{CE} = 200V)	0.4	5	3
H11D2			5300							
H11D3										
H11D4		10				200	100 (V _{CE} = 100V)			

Coupler Package Drawings

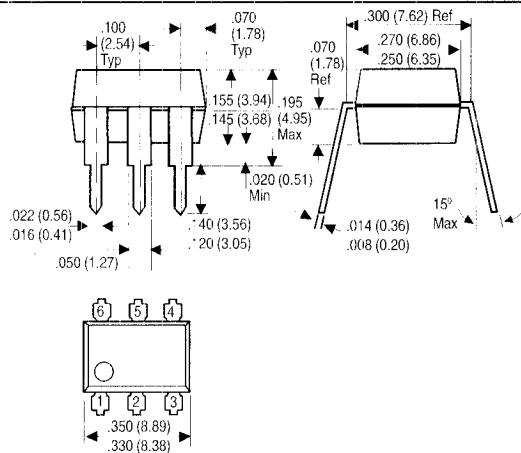
1



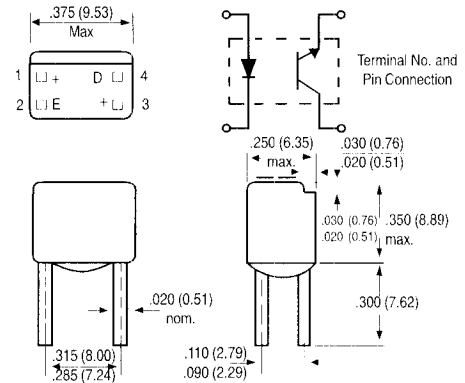
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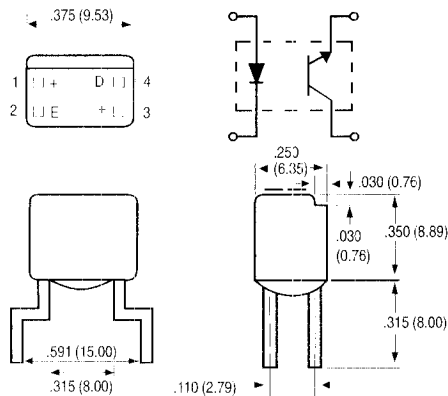
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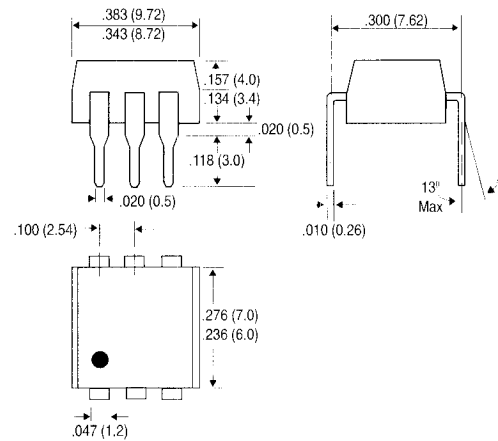
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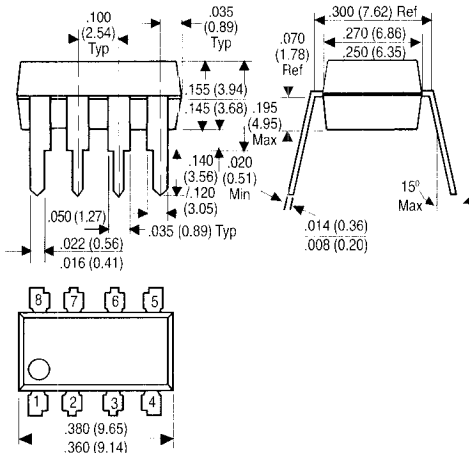
5



6



7



9



Coupler Schematics

